

AmendmentIn the Claims:

Please cancel claims 10-19. Please amend claims 1 and 20. Please add new claims 21-

30. The claims are as follows:

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1, (CURRENTLY AMENDED) An electronic structure comprising:

a substrate having a dielectric layer between a first metal layer and a second metal layer, the second metal layer being disposed above the first metal layer, the first metal layer having a first contact area, the second metal layer having a top surface that includes a selected area disposed above the first contact area;

a microvia cavity within the selected area being disposed through the second metal layer and through the dielectric layer and extending to the first contact area of the first metal layer; and

a mass of a single conductive material forming a layer upon the selected area of the top surface of the second metal layer and totally filling the microvia cavity and being in contact with the first contact area of the first metal layer.

2. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the mass of the single conductive material conformally fills the microvia cavity.

3. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the mass of the single conductive material has a planar surface forming a contact pad located parallel to and opposite the first contact area of the first metal layer.

4. (PREVIOUSLY AMENDED) The structure of claim 1, wherein selected area is approximately centered around the first contact area.

5. (PREVIOUSLY AMENDED) The structure of claim 4, wherein the second metal layer within the selected area is approximately centered around the microvia cavity.

6. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the second metal layer within the selected area is approximately centered around the first contact area.

7. The structure of claim 1, wherein the second metal layer contains a flat copper ring around the microvia cavity.

8. The structure of claim 1, wherein the microvia cavity includes a truncated cone-shaped hole in the dielectric layer.

9. (PREVIOUSLY AMENDED) The structure of claim 1, wherein the mass of the single conductive material comprises at least one of a solder paste, a reflowable solder, a conductive paste, and a conductive adhesive.

10-19. (CANCELED)

20. (CURRENTLY AMENDED) An assembly comprising:

a semiconductor chip;

a substrate having a dielectric layer between a first metal layer and a second metal layer, the second metal layer being disposed above the first metal layer, the first metal layer having a first contact area, the second metal layer having a top surface that includes a selected area disposed above the first contact area;

a microvia cavity within the selected area being disposed through the second metal layer and through the dielectric layer and extending to the first contact area of the first metal layer; and

a mass of a single conductive material forming a layer upon the selected area of the top surface of the second metal layer and totally filling the microvia cavity and being in contact with the first contact area of the first metal layer, wherein the semiconductor chip is electrically connected to the mass of the single conductive material.

21. (NEW) The assembly of claim 20, wherein the selected area is a planar area.

22. (NEW) The assembly of claim 20, wherein the selected area is a planar area that is about parallel to a planar top surface of the first metal layer.

23. (NEW) The assembly of claim 20, wherein an etch rate of the single conductive material is less than an etch rate of a metal comprised by the second metal layer.

24. (NEW) The assembly of claim 20, wherein the single conductive material is bondable to a wall of the microvia cavity.

25. (NEW) The assembly of claim 20, wherein the single conductive material is not bondable to a wall of the microvia cavity. (N)

26. (NEW) The structure of claim 1, wherein the selected area is a planar area. ok

27. (NEW) The structure of claim 1, wherein the selected area is a planar area that is about parallel to a planar top surface of the first metal layer. (ok)

28. (NEW) The structure of claim 1, wherein an etch rate of the single conductive material is less than an etch rate of a metal comprised by the second metal layer. (N)

29. (NEW) The structure of claim 1, wherein the single conductive material is bondable to a wall of the microvia cavity. (N)

30. (NEW) The structure of claim 1, wherein the single conductive material is not bondable to a wall of the microvia cavity. (N)